



型号/TYPE: SLS9926

SLS9926采用先进的沟槽技术，提供卓越的RDS（ON）和低栅电荷。防静电。该装置适合作为单向或双向负载开关，其共用漏极配置更方便。

The SLS9926 uses advanced trench technology to provide excellent RDS(ON) and low gate charge. It is ESD protected. This device is suitable for use as a uni-directional or bi-directional load switch, facilitated by its common-drain configuration.

主要特性/Features

先进的沟槽工艺技术 Advanced trench process technology

高密度单元设计，超低导通电阻 High density cell design for ultra low on-resistance

高功率和电流处理能力 High power and current handling capability

适用于锂电池组应用 Ideal for Li-ion battery pack applications

应用/Application

N沟道功率mosfet N-Channel Power MOSFET

笔记本电源管理 Power Management in Note book

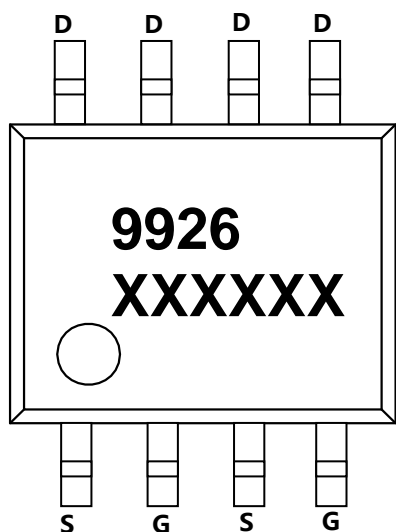
便携式设备 Portable Equipment

电池供电系统 Battery Powered System

负荷开关 Load Switch

DSC DSC

印字/MARKING 引脚定义/pin definition





极限参数/Absolute Maximum Ratings (TA=25°C Unless Otherwise Noted)

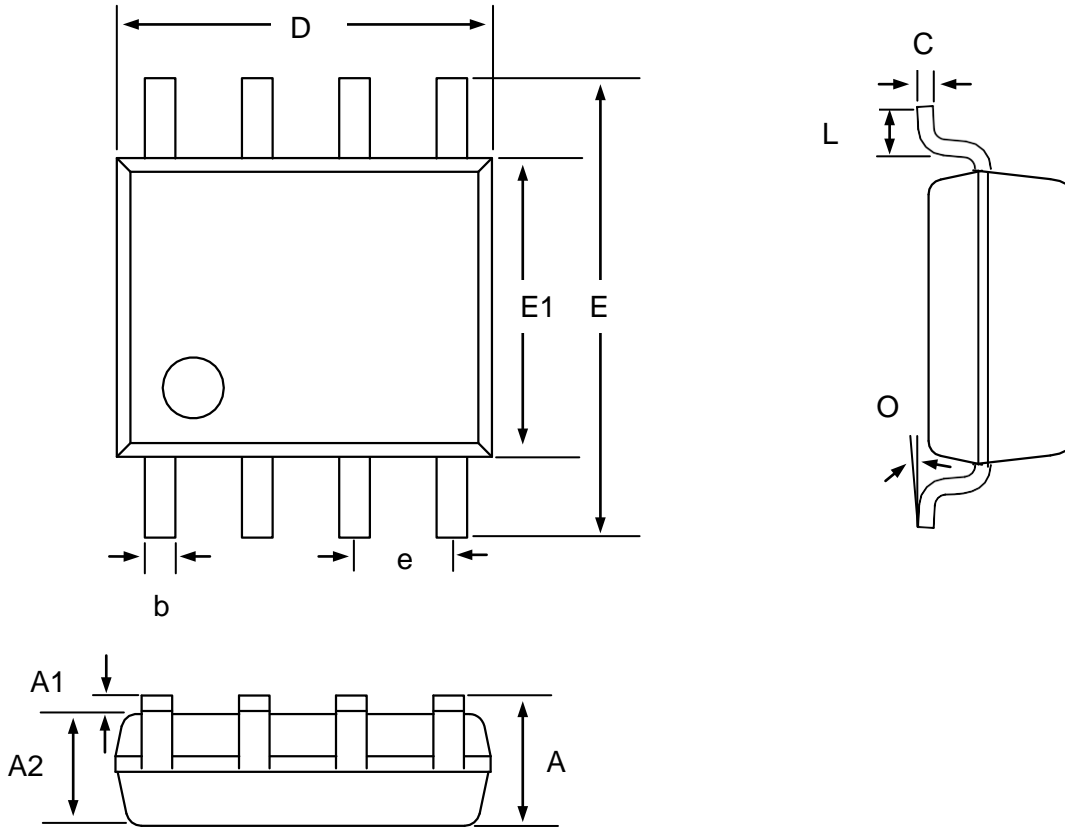
参数Parameter	符号Symbol	数值Value	单位Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	4.8	A
Pulsed Drain Current (note1)	I_{DM}	20	A
Power Dissipation	P_D (Ta=25°C)	1.15	W
Thermal Resistance Junction to Ambient(note2)	$R_{\theta JA}$	100	°C/mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 ~ 150	°C

电性能参数/Electrical Characteristics (TA=25°C unless otherwise noted)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
静态参数/Static Characteristics						
Drain-Source Breakdown Voltage	$V_{BR(DSS)}$	$V_{GS}=0V, I_D=250\mu A$	20			V
Gate Threshold Voltage(note3)	$V_{GS(th)}$	$I_D=250\mu A, V_{GS}=V_{DS}$	0.5		1.2	V
Gate-body leakage current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$			± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS}=18V, V_{GS}=0V$			1	μA
Drain-source on-resistance(note3)	$R_{DS(ON)}$	$V_{GS}=4.5V, I_D=6A$			30	m Ω
		$V_{GS}=2.5V, I_D=5.0A$			40	
Drain-Source Diode Forward Voltage(note3)	V_{SD}	$V_{GS}=0V, I_{SD}=1.7A$	0.5		1.2	V
动态参数/Dynamic Characteristics(note4)						
Input Capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0V,$ $f=1MHz$		620		pF
Output Capacitance	C_{oss}			150		
Reverse Transfer Capacitance	C_{rss}			80		
开关参数/Switching Characteristics(note4)						
Turn-on delay time	$t_{d(on)}$	$V_{DD}=15V, I_{DS}=1A,$ $V_{GEN}=4.5V, R_L=15\Omega,$ $R_{GEN}=6\Omega,$			35	ns
Turn-on rise time	t_r				55	ns
Turn-off delay time	$t_{d(off)}$				75	ns
Turn-off fall time	t_f				30	ns



封装外观尺寸/SOP8 Package Information



Symbol	Dim in mm		
	Min	Nor	Max
A	1.350	1.550	1.750
A1	0.100	0.175	0.250
A2	1.350	1.450	1.550
b	0.330	0.420	0.510
c	0.170	0.210	0.250
D	4.800	4.900	5.000
e	1.270(BSC)		
E	3.800	3.900	4.000
E1	0.400	0.835	1.2700
L	0°	4°	8°